# **Quad 2-Channel Multiplexer**

The MC74VHC157 is an advanced high-speed CMOS quad 2-channel multiplexer, fabricated with silicon gate CMOS technology. It achieves high-speed operation similar to equivalent Bipolar-Schottky TTL, while maintaining CMOS low-power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable  $(\overline{E})$  inputs. When  $\overline{E}$  is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 4.1 \text{ ns (Typ)}$  at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 82 FETs
- These Devices are Pb-Free and are RoHS Compliant

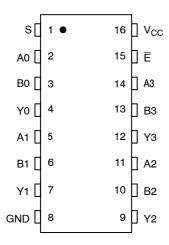


Figure 1. Pin Assignment



#### ON Semiconductor

http://onsemi.com

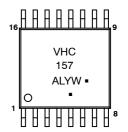
#### MARKING DIAGRAMS







CASE 948F



VHC157 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping
MC74VHC157DR2G	SOIC-16	2500 Units/Reel
MC74VHC157DTR2G	TSSOP-16	2500 Units/Reel

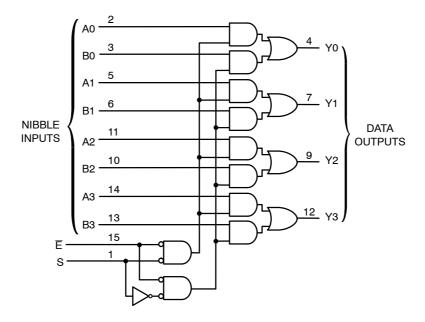


Figure 2. Expanded Logic Diagram

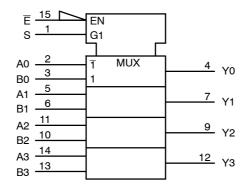


Figure 3. IEC Logic Symbol

#### **FUNCTION TABLE**

Inp	Outputs	
Ē	Y0 – Y3	
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

A0 - A3, B0 - B3 = the levels of the respective Data-Word Inputs.

#### **MAXIMUM RATINGS** (Note 1)

Symbol	Pa	rameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5 to V <sub>CC</sub> +7.0	V
Vo	DC Output Voltage		$-0.5$ to $V_{CC}$ +7.0	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	$V_{O} < GND$	±20	mA
I <sub>O</sub>	DC Output Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		± 100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for	10 Seconds	260	°C
$T_{J}$	Junction Temperature under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance		250	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% - 35%	UL-94-VO (0.125 in)	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I <sub>Latch-Up</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 5)	±500	mA

<sup>1.</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage (Note 6)	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types	- 55	125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $ \begin{array}{c} V_{CC} = 3.3 \ V \ \pm \ 0.3 \ V \\ V_{CC} = 5.0 \ V \ \pm \ 0.5 \ V \end{array} $	0 0	100 20	ns/V

<sup>6.</sup> Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

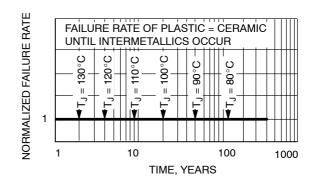


Figure 4. Failure Rate vs. Time Junction Temperature

<sup>2.</sup> Tested to EIA/JESD22-A114-A.

<sup>3.</sup> Tested to EIA/JESD22-A115-A.

<sup>4.</sup> Tested to JESD22-C101-A.

Tested to EIA/JESD78.

#### DC CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	Т	A = 25°	2	T <sub>A</sub> ≤	85°C	-55°C ≤T	_ <sub>A</sub> ≤125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 to 5.5	1.5 0.7 V <sub>CC</sub>			1.5 0.7 V <sub>CC</sub>		1.5 0.7 V <sub>CC</sub>		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 to 5.5			0.5 0.3 V <sub>CC</sub>		0.5 0.3 V <sub>CC</sub>		0.5 0.3 V <sub>CC</sub>	V
V <sub>OH</sub>	High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V <sub>OL</sub>	Low-Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = 4$ mA $I_{OH} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μΑ

#### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

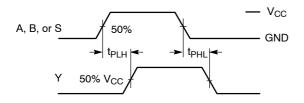
					T <sub>A</sub> = 25°	С	<b>T</b> <sub>A</sub> ≤85°C		–55°C ≤T	A ≤ 125°C	
Symbol	Characteristic	Test Condit	ions	Min	Тур	Max	Тур	Max	Тур	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A to B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.2 8.7	9.7 13.2	1.0 1.0	11.5 15.0	1.0 1.0	11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, S to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		8.4 10.9	13.2 16.7	1.0 1.0	15.5 19.0	1.0 1.0	15.5 19.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, E to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		8.7 11.2	13.6 17.1	1.0 1.0	16.0 19.5	1.0 1.0	16.0 19.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C <sub>IN</sub>	Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 7)	20	pF

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

### **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0 \text{ ns}$ ; $C_L = 50 \text{ pF}$ ; $V_{CC} = 5.0 \text{ V}$ )

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V



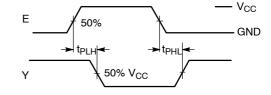
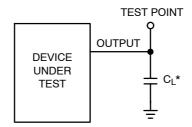


Figure 5. Switching Waveform

Figure 6. Inverting Switching



<sup>\*</sup>Includes all probe and jig capacitance.

Figure 7. Test Circuit

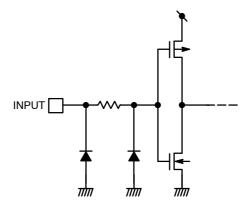
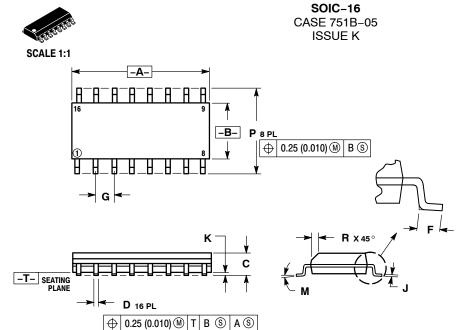


Figure 8. Input Equivalent Circuit

## **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR EMITTER COLLECTOR COLLECTOR COLLECTOR	2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION	STYLE 3: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15. 16.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3 COLLECTOR, #3 COLLECTOR, #4 BASE, #4 EMITTER, #4 COLLECTOR, #4	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15. 16.	COLLECTOR, DYE COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2 EMITTER, #2 BASE, #1 EMITTER, #1	SOLDERING FOOTPRINT  SX 6.40  H  SX  SX  SX  SX  SX  SX  SX  SX  SX	
STYLE 5: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, DYE #1 DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #2 SOURCE, #3 GATE, #2 SOURCE, #1 SOURCE, #1	3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	STYLE 7: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15.	SOURCE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT SOURCE N-CH		16 0.£	16X 1.12	1.27 PITCH

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	SOIC-16		PAGE 1 OF 1

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

☐ 0.10 (0.004)

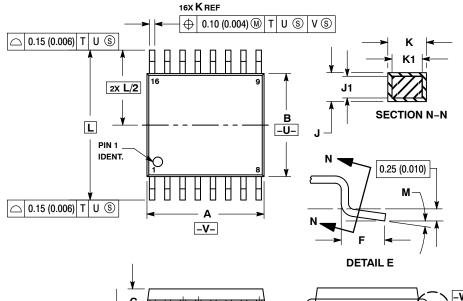
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



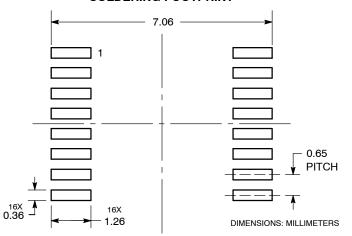
#### NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8°	0 °	8 °

#### **SOLDERING FOOTPRINT**

G



#### **GENERIC MARKING DIAGRAM\***

168888888 XXXX XXXX **ALYW** 1<del>88888888</del>

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70247A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-16		PAGE 1 OF 1	

**DETAIL E** 

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales